

Plastic-Encapsulate Thyristors

Silicon Controlled Rectifier

FEATURES

Current- I_{GT} : 200 μA

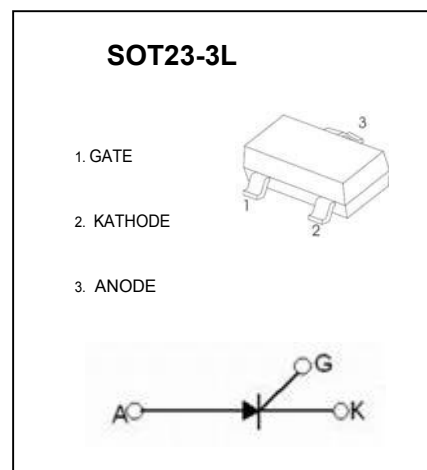
I_{TRMS} : 0.8 A

V_{RRM}/V_{DRM} : MCRN100-6: 400 V

MCRN100-8: 600 V

Operating and storage junction temperature range T_J ,

T_{stg} : -55°C to +150°C



ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
On state voltage	V_{TM}^*	$I_{TM}=1A$		1.7	V
Gate trigger voltage	V_{GT}	$V_{AK}=7V$		0.8	V
Peak Repetitive forward and reverse blocking voltage MCRN100-6 MCRN100-8	V_{DRM} AND V_{RRM}	$I_{DRM}=10\mu A$	400 600		V
Peak forward or reverse blocking Current	I_{DRM} I_{RRM}	$V_{AK}=Rated$ V_{DRM} or V_{RRM}		10	μA
Holding current	I_H	$I_{HL}=20mA, V_{AK}=7V$		5	mA
Gate trigger current	I_{GT}	$V_{AK}=7V$	5	15	μA
			15	30	μA
			30	80	μA
			80	200	μA

* Forward current applied for 1 ms maximum duration, duty cycle $\leq 1\%$.

Typical Characteristics

